JST236W-800D

(T_j=25 unless otherwise specified)

Symbol	**Test Condition**	**Quadrant**	**Value**		**Unit**
I_{GT}	V_D=12V R_L=33Ω	- -	MAX.	5	mA
				10	
V_{GT}		ALL	MAX.	1.3	V

V_{GD}

V V

DRM

3.

J ST 236 W -800

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

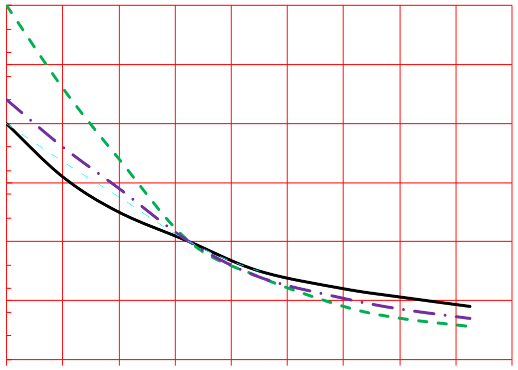

FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards